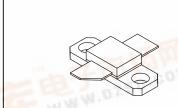
The RF Line NPN Silicon RF Power Transistor

Designed for 28 Volt microwave large—signal, common base, Class—C CW amplifier applications in the range 1600 – 1640 MHz.

- Specified 28 Volt, 1.6 GHz Class–C Characteristics
 Output Power = 6 Watts
 Minimum Gain = 7.4 dB, @ 6 Watts
 Minimum Efficiency = 40% @ 6 Watts
- Characterized with Series Equivalent Large—Signal Parameters from 1500 MHz to 1700 MHz
- Silicon Nitride Passivated
- Gold Metallized, Emitter Ballasted for Long Life and Resistance to Metal Migration
- Circuit board photomaster available upon request by contacting RF Tactical Marketing in Phoenix, AZ.

MRF16006

6.0 WATTS, 1.6 GHz RF POWER TRANSISTOR NPN SILICON



CASE 395C-01, STYLE 2

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	VCES	60	Vdc
Emitter-Base Voltage	VEBO	4.0	Vdc
Collector–Current	IC	1.0	Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	26 0.15	Watts W/°C
Storage Temperature Range	T _{stg}	-65 to +150	°C

THERMAL CHARACTERISTICS

Thermal Resistance — Junction to Case (1) (2)	$R_{\theta JC}$	6.8	°C/W
	000		1

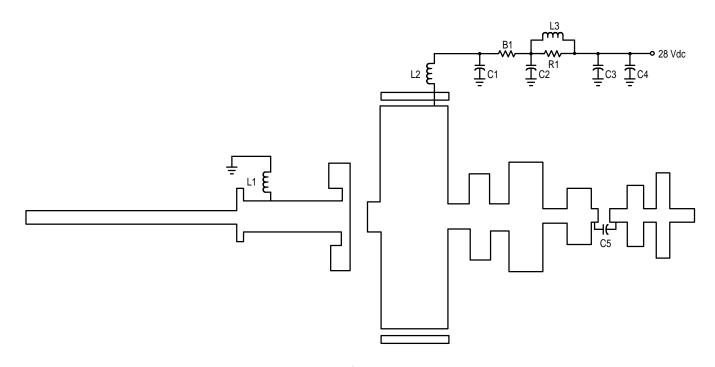
- (1) Thermal measurement performed using CW RF operating condition.
- (2) Thermal resistance is determined under specified RF operating conditions by infrared measurement techniques.





ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

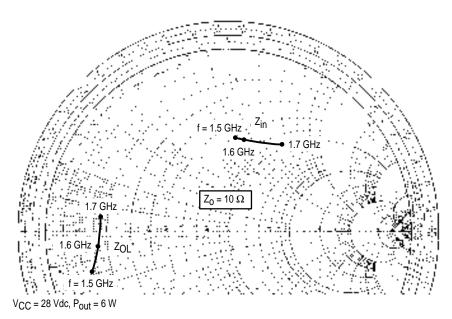
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					<u> </u>
Collector–Emitter Breakdown Voltage (I _C = 40 mAdc, V _{BE} = 0)	V _(BR) CES	55	_	_	Vdc
Collector–Base Breakdown Voltage (I _C = 40 mAdc, I _E = 0)	V(BR)CBO	55	_	_	Vdc
Emitter–Base Breakdown Voltage (I _E = 2.5 mAdc, I _C = 0)	V(BR)EBO	4.0	_	_	Vdc
Collector Cutoff Current (VCE = 28 Vdc, V _{BE} = 0)	ICES	_	_	2.5	mAdc
ON CHARACTERISTICS					
DC Current Gain (I _{CE} = 0.2 Adc, V _{CE} = 5.0 Vdc)	hFE	20	_	80	_
DYNAMIC CHARACTERISTICS				•	•
Output Capacitance (V _{CB} = 28 Vdc, f = 1.0 MHz)	C _{ob}	11	_	_	pf
FUNCTIONAL TESTS				•	•
Common–Base Amplifier Power Gain (V _{CC} = 28 Vdc, P _{Out} = 6 Watts, f = 1600/1640 MHz)	G _{pe}	7.4	_	_	dB
Collector Efficiency (V _{CC} = 28 Vdc, P _{out} = 6 Watts, f = 1600/1640 MHz)	η	40	45	_	%
Return Loss (V _{CC} = 28 Vdc, P _{out} = 6 Watts, f = 1600/1640 MHz)	I _{RL}	_	8.0	_	dB
Output Mismatch Stress (V _{CC} = 28 Vdc, P _{Out} = 6 Watts, f = 1600 MHz, Load VSWR = 3:1 all phase angles at frequency of test)	Ψ	No E	Degradation in	Output Powe	er



Board Material – Teflon® Glass Laminate Dielectric Thickness – 0.30″, ϵ_Γ = 2.55″, 2.0 oz. Copper

B1 Fair Rite Bead on #24 Wire C4 $47 \mu F$, 50 V, Electrolytic Cap 100 pF, B Case, ATC Chip Cap C1, C5 3 Turns, #18, 0.133" ID, 0.15" Long L1, L2 C2 0.1 μF, Dipped Mica Cap L3 9 Turns, #24 Enamel СЗ $0.1~\mu\text{F}$, Chip Cap R1 82 Ω , 1.0 W, Carbon Resistor

Figure 1. MRF16006 Test Fixture Schematic



f MHz	Z _{in} Ohms	Z _{OL} * Ohms
1500	6.28 + j 8.53	1.22 – j 1.37
1600	7.04 + j 9.00	1.58 – j 0.53
1700	9.55 + j 12.86	1.71 + j 0.39

 Z_{OL}^{\star} = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage and frequency.

Figure 2. Series Equivalent Input/Output Impedance

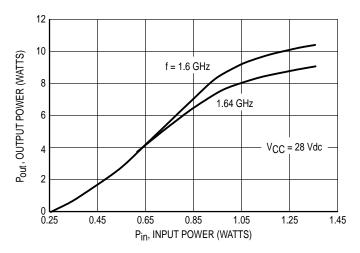
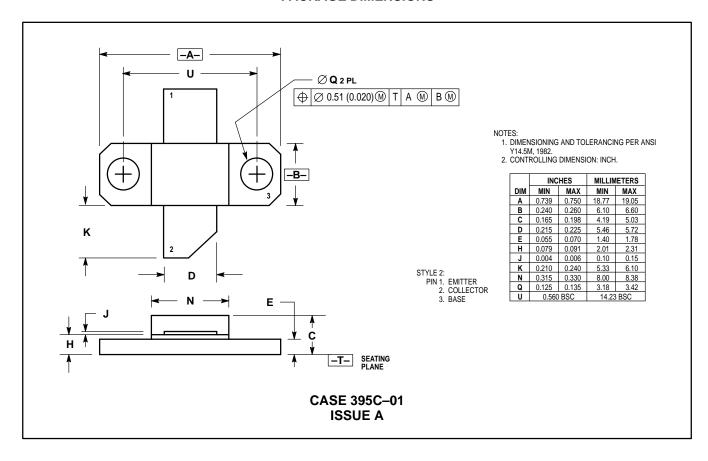


Figure 3. Output Power versus Input Power

PACKAGE DIMENSIONS



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